

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

BREV 12370 CON4

Application Number

10/784,601

Applicant(s)

ASPAR et al.

Filing Date

February 23, 2004

Group Art Unit

2812/2823

U.S. PATENT DOCUMENTS

INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
G		SU 1282757	12.30.83	RUSSIA	H01L	21/265		

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

FOURSON

DATE CONSIDERED

9/17/05

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				Applicant(s) ASPAR et al.			
				Filing Date February 23, 2004		Group Art Unit 2812 2823	

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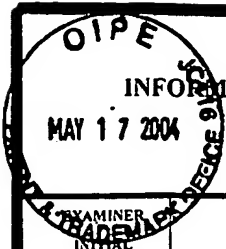
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G		Reissue App. 10/449,786					

FOREIGN PATENT DOCUMENTS								
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							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER Fourson	DATE CONSIDERED 9/17/05
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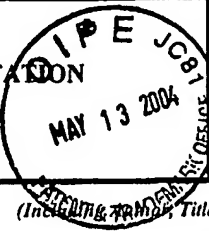
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BREV 12370 N3

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INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

BREV 12370 (13

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09/777-516

Applicant(s)

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Docket Number (Optional)

BREV 12370 C

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10/784/01

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ASPAR ET AL

Filing Date

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EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
DRG		5,256,581	10/26/93	FOERSTNER ET AL	437	24	
DRG		6,020,252	2/1/00	ASPAR ET AL	438	458	

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

D.B. Courts FOURSON

DATE CONSIDERED

12-21-01 9/17/05

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INFORMATION DISCLOSURE CITATION
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BREV 12370 CON 2

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<i>G</i>	5,234,535	8/10/93	NBeyer et al			
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<i>G</i>	5,250,446	10/5/93	Osowa et al			

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						YES	NO
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<i>G</i>	EP 0703 609	3/27/96	EPO			✓	
	0 660 140	6/28/95	EPO			✓	
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12-24-07 9/12/05

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INFORMATION DISCLOSURE STATEMENT
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Aspar et al

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FORM PTO-1449	SERIAL NO. 10/784601	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE	GROUP ART UNIT 2823
(use several sheets if necessary)	APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION

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U.S. PATENTS

<u>PATENT NO.</u>	<u>INVENTOR</u>	<u>ISSUE DATE</u>
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5,110,748	5/5/92	Sarma
5,310,446	5/10/94	Konishi et al.
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<u>DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>DATE</u>
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<i>DRC</i>	A1	4,179,324	12/18/79	Kirkpatrick	156/230	11/28/77
<i>G</i>	A2	5,110,748	5/5/92	Sarma	437/51	7/22/91
<i>G</i>	A3	5,310,446	5/10/94	Konishi et al.	117/58	7/13/92
<i>G</i>	A4	5,661,333	8/26/97	Bruel et al.	257/618	1/25/95
	A5					
	A6					
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	A8					

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES	NO
<i>DRC</i>	A9	2725074	3/29/96	France			X
<i>G</i>	A10	0355913	2/28/90	EPO		X	
<i>G</i>	A11	0504714	9/23/92	EPO		X	

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<i>G</i>	A13	Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEMI</i> 1996, pp. 37-46
<i>G</i>	A14	Klem et al., Characteristics of lift-off fabricated AlGaAs/InGaAs single-strained quantum well structures on glass and silicon substrates, <i>Inst. Phys. Conf.</i> , Ser. No 96: Chapter 6, pp. 387-392
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						YES	NO
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<p><i>D.M. Collins</i> <i>Ferguson</i></p>		<p><i>12-21-01</i> <i>7/17/05</i></p>

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